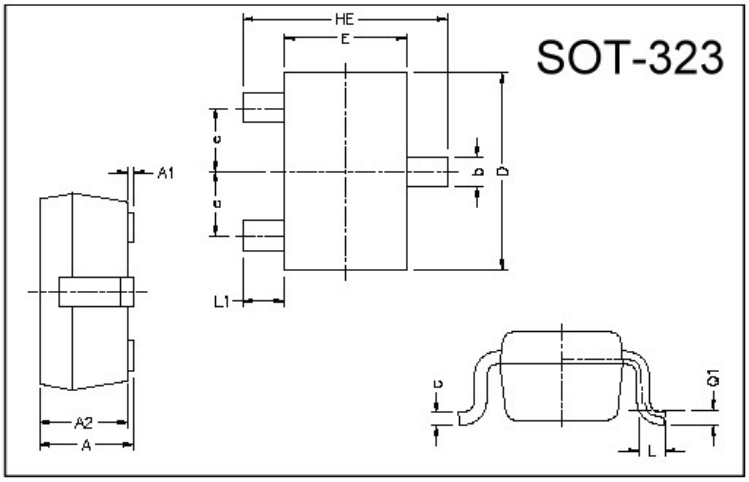
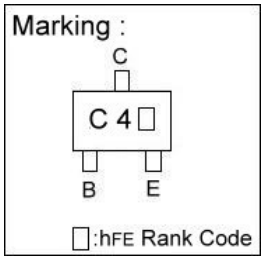
GSMBT1815 NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GSMBT1815 is designed for use in driver stage of AF amplifier and general purpose amplification.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55~+150	℃
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	50	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	150	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25℃

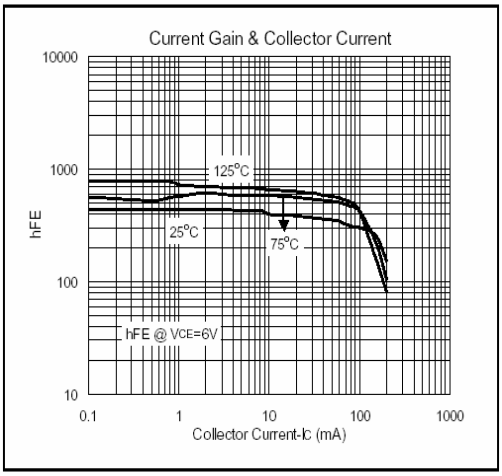
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=100uA
BVCEO	50	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICBO	-	-	100	nA	VCB=60V
IEBO	-	-	100	nA	VEB=5V
*VCE(sat)	-	-	250	mV	IC=100mA, IB=10mA
*VBE(sat)	-	-	1	V	IC=100mA, IB=10mA
*hFE1	120	-	700		VCE=6V, IC=2mA
*hFE2	25	-	-		VCE=6V, IC=150mA
fT	80	-	-	MHz	VCE=10V, IC=1mA, f=100MHz
Cob	-	-	3.5	pF	VCB=10V, f=1MHz

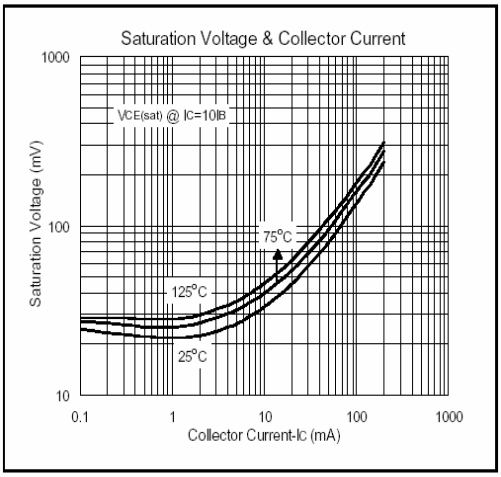
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

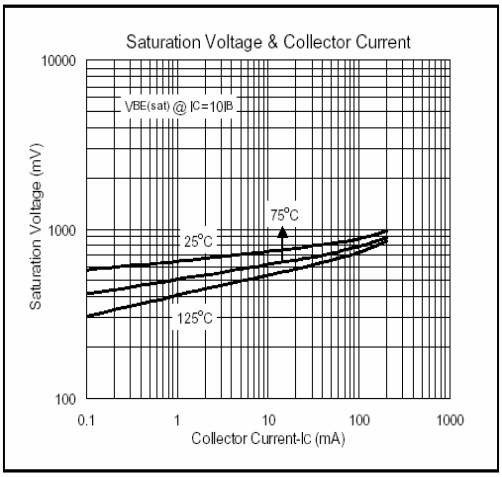
Classification Of hFE1

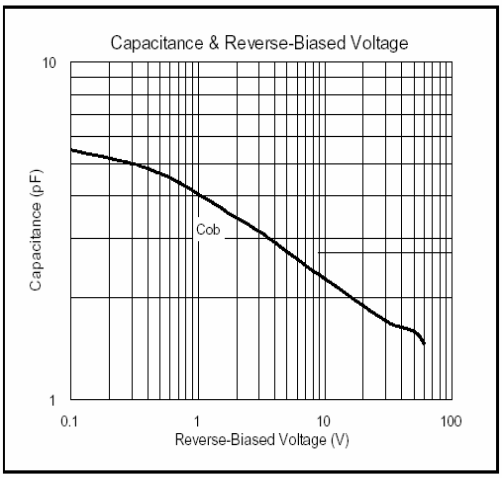
Rank	C4Y	C4G	C4B
Range	120 - 240	200 - 400	350 - 700

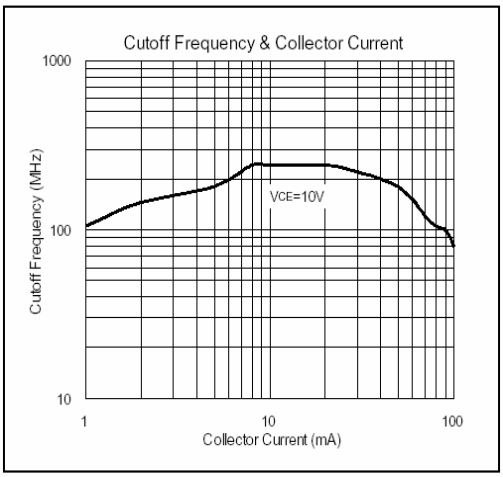
Characteristics Curve

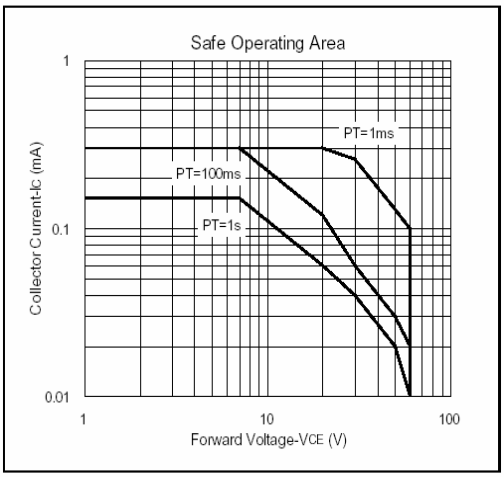












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